## 1. General description

Logic level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 2. Features and benefits

- Enhanced forward biased safe operating area for superior linear mode operation
- Very low Rdson for low conduction losses

## 3. Applications

- Electronic fuse
- Hot swap
- · Load switch
- Soft start

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	238	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics					'	
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 12		-	1.7	2	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 12		-	3	3.5	mΩ
Dynamic ch	naracteristics			'		<u> </u>	
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; Fig. 14; Fig. 15		-	13.8	-	nC
$Q_{G(tot)}$	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15		-	87	-	nC
Avalanche i	ruggedness		'				
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 100 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4		-	-	365	mJ



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain diode							
Q <sub>r</sub>	recovered charge	$I_S$ = 25 A; $dI_S/dt$ = 100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 15 V		-	49.8	-	nC

[1] Capped at 100A due to package

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	
2	S	source	<u> </u>	D
3	S	source		
4	G	gate	0 0 0 0	G_(□□□□□)
mb	D	mounting base; connected to drain	LFPAK56; Power- SO8 (SOT669)	mbb076 S

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PSMN2R0-30YLE	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669		

## 7. Marking

## Table 4. Marking codes

Type number	Marking code
PSMN2R0-30YLE	2E0L30Y

# 8. Limiting values

## **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	30	V
$V_{DGR}$	drain-gate voltage	$25 \degree C ≤ Tj ≤ 175 \degree C; RGS = 20 kΩ$		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	238	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	100	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	1015	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain d	iode		'			'
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	1015	Α
Avalanche rug	gedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 100 A; $V_{sup} \le 30$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4		-	365	mJ

### [1] Capped at 100A due to package

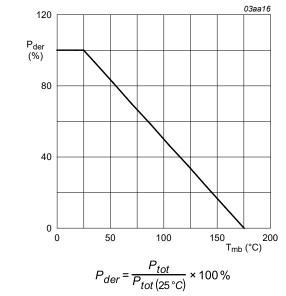


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

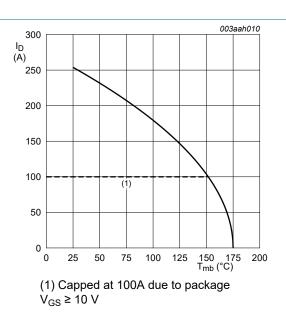
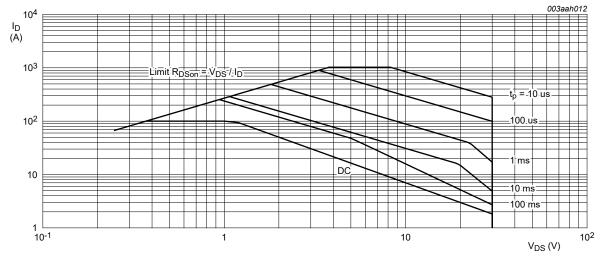
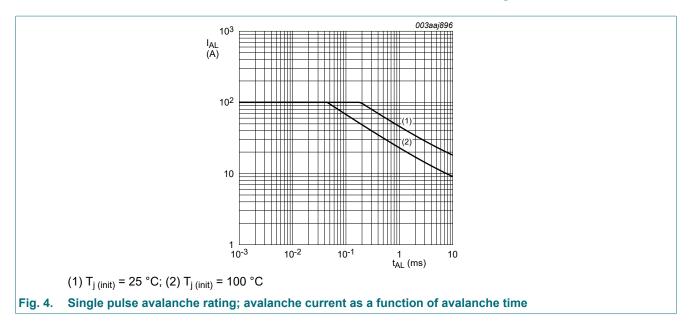


Fig. 2. Continuous drain current as a function of mounting base temperature



T<sub>mb</sub> = 25 °C; I<sub>DM</sub> is a single pulse

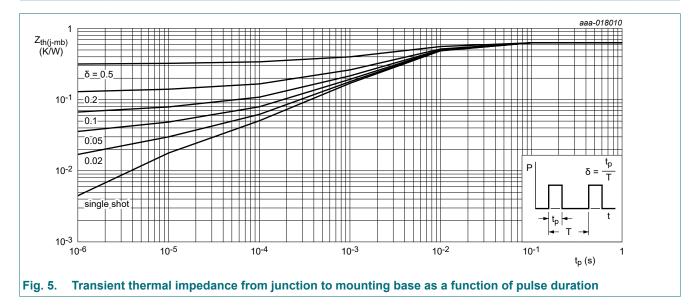
Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.55	0.63	K/W



## 10. Characteristics

**Table 7. Characteristics** 

Tubio II Gila								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static chara	Static characteristics							
V <sub>(BR)DSS</sub>	brookdown voltago	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$		27	-	-	V	
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		30	-	-	V	

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 10; Fig. 11$	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 10$	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 100 \text{ °C}$	-	-	200	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	10	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 12	-	1.7	2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 12; Fig. 13	-	-	2.8	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 12	-	3	3.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13	-	-	3.8	mΩ
$R_G$	gate resistance	f = 1 MHz	0.3	0.6	1.2	Ω
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	87	-	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; Fig. 14; Fig. 15	-	41	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	79	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	13.3	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 14; Fig. 15	-	8.1	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	5.2	-	nC
$Q_GD$	gate-drain charge		-	13.8	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	2.8	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	5217	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	1015	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	474	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$	-	32.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$	-	55.7	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	41.5	-	ns
t <sub>f</sub>	fall time		-	29.5	-	ns
Source-drai	in diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 17</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	42.6	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V	-	49.8	-	nC

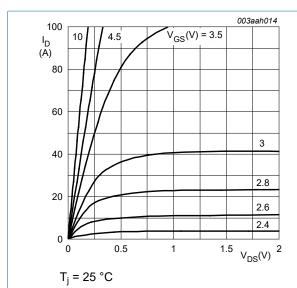


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

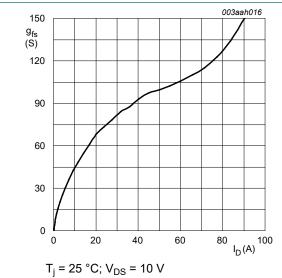


Fig. 8. Forward transconductance as a function of drain current; typical values

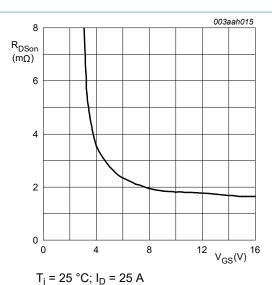


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

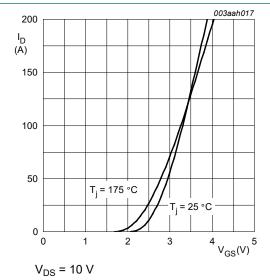


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

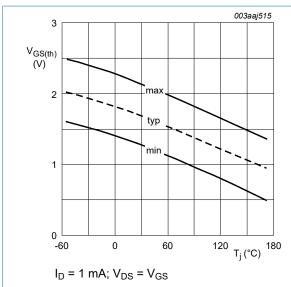


Fig. 10. Gate-source threshold voltage as a function of junction temperature

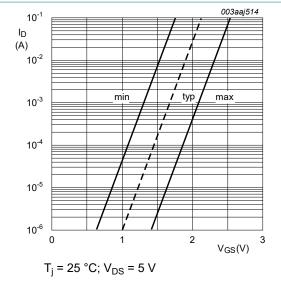


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

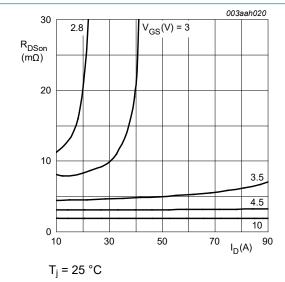


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

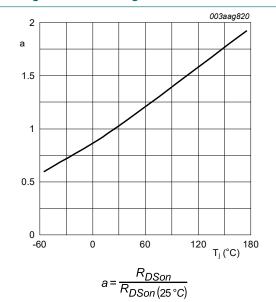


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

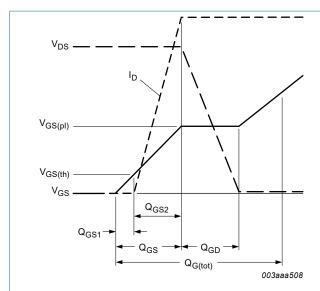


Fig. 14. Gate charge waveform definitions

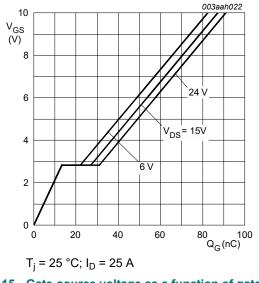


Fig. 15. Gate-source voltage as a function of gate charge; typical values

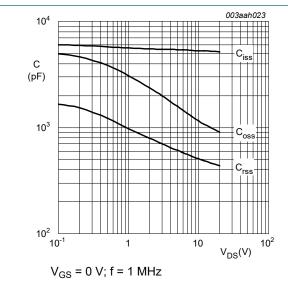
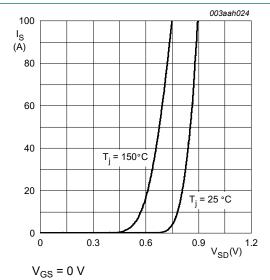


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source current as a function of source-drain as a function of drain-source voltage; typical values



voltage; typical values

# 11. Package outline

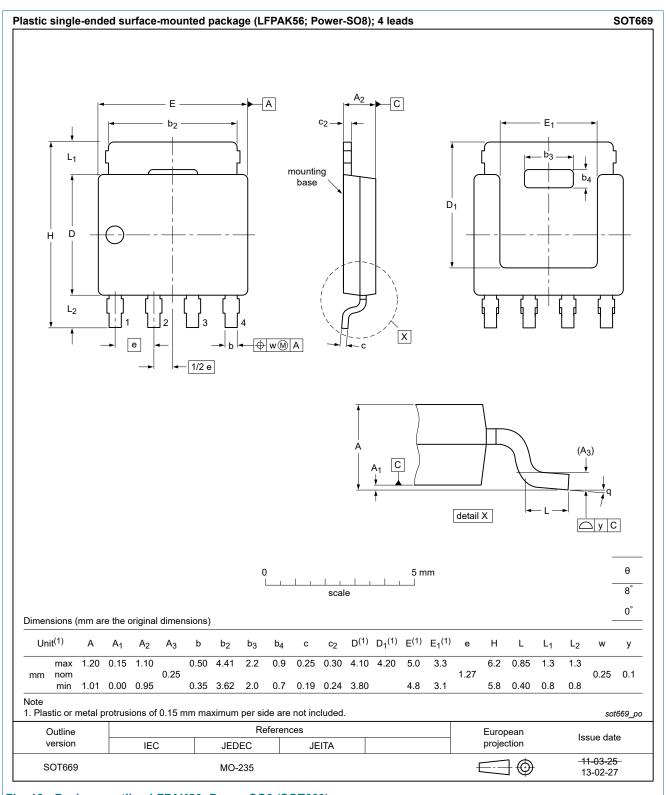
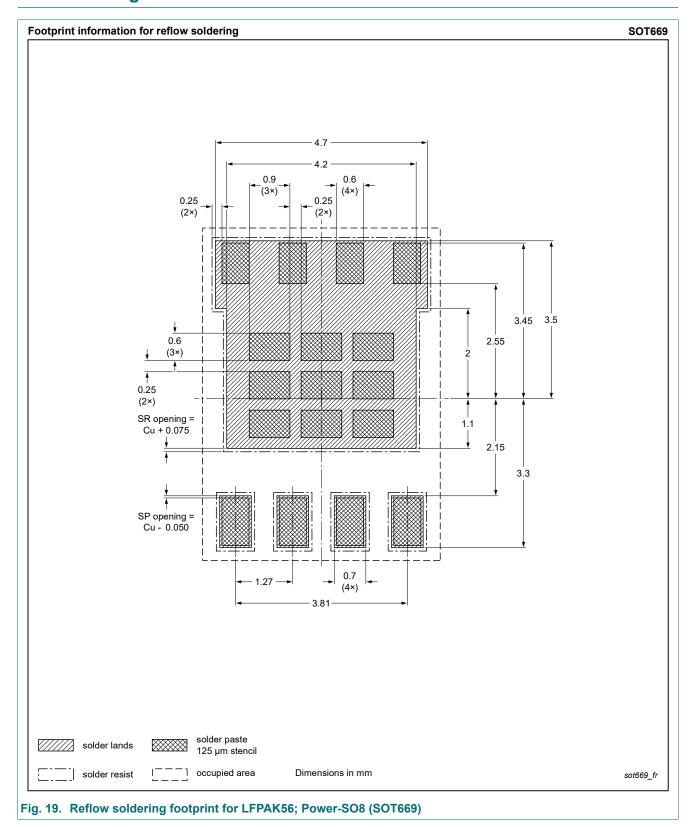


Fig. 18. Package outline LFPAK56; Power-SO8 (SOT669)

# 12. Soldering



10 / 13

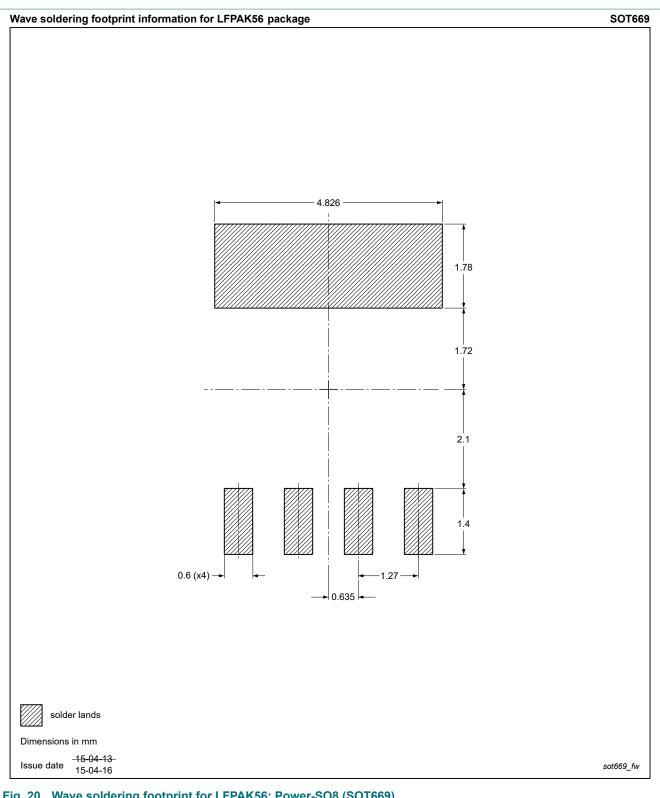


Fig. 20. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

## 13. Legal information

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#### N-channel 30 V 2 mΩ logic level MOSFET in LFPAK

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## **Contents**

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	2
	Thermal characteristics	
10	. Characteristics	4
11.	. Package outline	9
	. Soldering	
	. Legal information	

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